

## In the Claims

Claims 1-68 (cancelled).

Claim 69 (original): A CMOS, comprising:

- a dielectric layer over a substrate;
- a PMOS gate and an NMOS gate over the dielectric layer;
- a first metal-containing material within the PMOS gate and over the dielectric layer, the first metal-containing material having a thickness of greater than 20Å;
- a second metal-containing material within the NMOS gate and over the dielectric layer, the second metal-containing material having a thickness of less than or equal to about 20Å;
- a first layer of n-type doped silicon within the PMOS gate and over the first metal-containing material; and
- a second layer of n-type doped silicon within the NMOS gate and over the second metal-containing material.

Claim 70 (original): The CMOS of claim 69 wherein the dielectric layer comprises one or more of tantalum, hafnium and aluminum.

Claim 71 (original): The CMOS of claim 69 wherein the dielectric layer comprises aluminum oxide.

Claim 72 (original): The CMOS of claim 71 wherein the first and second metal-containing materials are physically against the aluminum oxide.

Claim 73 (original): The CMOS of claim 69 wherein the first and second metal-containing materials have the same composition as one another.

Claim 74 (original): The CMOS of claim 73 wherein the first and second metal-containing materials predominately comprise one or more of titanium nitride, tantalum nitride, tungsten nitride and hafnium nitride.

Claim 75 (original): The CMOS of claim 73 wherein the first and second metal-containing materials predominately comprise one or more of titanium silicide, tantalum silicide, tungsten silicide and hafnium silicide.

Claim 76 (original): The CMOS of claim 69 wherein the thickness of the second metal-containing material is less than or equal to about 15Å.

Claim 77 (original): The CMOS of claim 69 wherein the thickness of the second metal-containing material is less than or equal to about 10Å.

Claim 78 (original): The CMOS of claim 69 wherein the thickness of the first metal-containing material is greater than or equal to about 100Å.

Claim 79 (original): The CMOS of claim 69 wherein the thickness of the first metal-containing material is greater than or equal to about 150Å.

Claim 80 (original): The CMOS of claim 69 wherein the thickness of the first metal-containing material is greater than or equal to about 150Å, and wherein the thickness of the second metal-containing material is less than or equal to about 15Å.

Claim 81 (original): An electronic system comprising the CMOS of claim 69.

Claim 82 (original): A capacitor construction, comprising:

- a first capacitor electrode, the first capacitor electrode comprising conductively-doped silicon;

- a dielectric layer proximate the first capacitor electrode;

- a second capacitor electrode across the dielectric layer from the first capacitor electrode; and

- a metal-containing material between the conductively-doped silicon of the first capacitor electrode and the dielectric layer, the metal-containing material having a thickness of less than or equal to about 20Å.

Claim 83 (original): The capacitor construction of claim 82 wherein the second capacitor electrode is a storage node of the capacitor.

Claim 84 (original): The capacitor construction of claim 83 wherein the second capacitor electrode comprises rugged silicon.

Claim 85 (original): The capacitor construction of claim 82 wherein the conductively-doped silicon is majority n-type doped.

Claim 86 (original): The capacitor construction of claim 82 wherein the dielectric layer comprises one or more of tantalum, hafnium and aluminum.

Claim 87 (original): The capacitor construction of claim 82 wherein the dielectric layer comprises aluminum oxide.

Claim 88 (original): The capacitor construction of claim 87 wherein the metal-containing material is physically against the aluminum oxide.

Claim 89 (original): The capacitor construction of claim 82 wherein the metal-containing material predominately comprises one or more of titanium nitride, tantalum nitride, tungsten nitride and hafnium nitride.

Claim 90 (original): The capacitor construction of claim 82 wherein the metal-containing material predominately comprises one or more of titanium silicide, tantalum silicide, tungsten silicide and hafnium silicide.

Claim 91 (original): The capacitor construction of claim 82 wherein the thickness of the metal-containing material is less than or equal to about 15Å.

Claim 92 (original): The capacitor construction of claim 82 wherein the thickness of the metal-containing material is less than or equal to about 10Å.

Claim 93 (original): A DRAM comprising the capacitor construction of claim 82.

Claim 94 (original): An electronic system comprising the DRAM of claim 93.